

TPR 1000

1000 Watts, 45 Volts, Pulsed Avionics 1090 MHz

GENERAL DESCRIPTION

The TPR 1000 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1090 MHz. The device has gold thin-film metallization for proven highest MTTF. The transistor includes input returns for **fast rise time**. Low thermal resistance package reduces junction temperature, extends life.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C² 2900 Watts

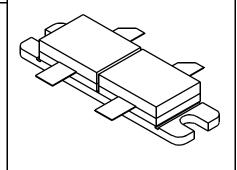
Maximum Voltage and Current

BVcesCollector to Base Voltage65 VoltsBVeboEmitter to Base Voltage3.5 VoltsIcCollector Current80 Amps

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 200^{\circ}\text{C}$ Operating Junction Temperature $+200^{\circ}\text{C}$

CASE OUTLINE 55KV, Style 1 Common Base



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg η _c	Power Out Power Input Power Gain Collector Efficiency	F = 1090 MHz Vcc = 45 Volts PW = 10 μsec DF = 1%	1000	43	250	Watts Watts dB %
t _r VSWR ¹	Rise Time Load Mismatch Tolerance	F = 1030 MHz			70 9:1	ns

Emitter to Base Breakdown	Ie = 50mA	3.5			Volts
Collector to Emitter Breakdown	Ic = 100mA	65			Volts
DC - Current Gain	Ic = 1000 mA, Vce = 5 V	10			
Thermal Resistance				0.06	°C/W
	Collector to Emitter Breakdown DC - Current Gain		Collector to Emitter Breakdown	Collector to Emitter Breakdown Ic = 100mA 65 DC - Current Gain Ic = 1000mA, Vce = 5 V 10	Collector to Emitter Breakdown Ic = 100mA 65 DC - Current Gain Ic = 1000mA, Vce = 5 V 10

Note 1: At rated output power and pulse conditions

2: At rated pulse conditions

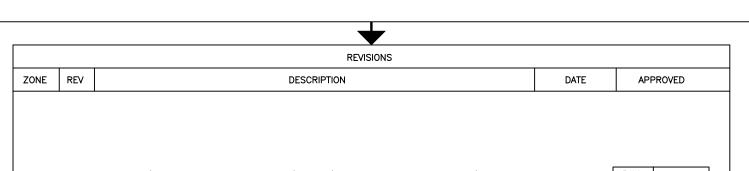
3: Cannot measure due to input return

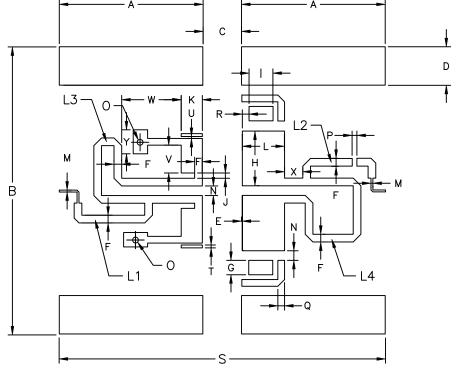
4: Per Side

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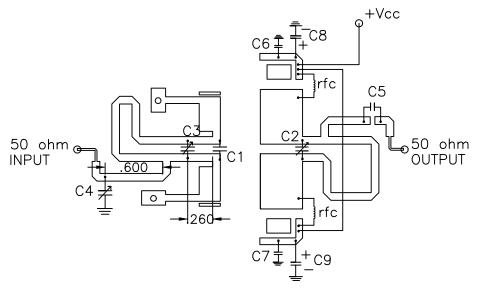
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DIM	INCHES	
Α	1.500	
В	3.000	
O	.406	
D	.4045	
E	.004	
F	.080	
G	.150	
Н	.569	
	.254	
J	.054	
K	.220	
L	.440	
М	.019	
N	.100	
0	ø0.060	
Р	.050	
Q	.074	
R	.079	
S	3.406	
Т	.030	
U	.020	
٧	.290	
W	0.615	
X	0.175	
Υ	0.250	
L1, L2	1.05	
L3, L4	2.10	



C1=4.7pf ATC B C2=1-10pf Voltronics EJ10HV.

C3,C4=.5-3.5pfJohnson

C5=47pf ATC B C6,C7=82pf ATC B

C8,C9=250MFD 60v

Board Type : Ceramic Er=10.2

Thk=.025inches.



CAGE DWG NO. TPR10		00	REV _	
- · · · · · · ·	SCALE	1/1	SHEET	